SanRex TRIACS

$I_{T(RMS)}$ 〔A〕		16amp (Tc=96℃) Harmetic	16amp (Tc=82℃) Harmetic Isolated	16amp (Tc=83℃) Mold Isolated	25amp (Tc=88℃) Harmetic	25amp (Tc=74℃) Harmetic Isolated	25amp (Tc=74℃) Mold Isolated	35amp (Tc=84℃) Harmetic	35amp (Tc=62℃) Harmetic Isolated
V_{DRM} 〔V〕	200	SSG16C20	SSG16C20Y	TG16C20	SSG25C20	SSG25C20Y	TG25C20	SSG35C20	SSG35C20Y
	300	SSG16C30	SSG16C30Y	TG16C30	SSG25C30	SSG25C30Y	TG25C30	SSG35C30	SSG35C30Y
	400	SSG16C40	SSG16C40Y	TG16C40	SSG25C40	SSG25C40Y	TG25C40	SSG35C40	SSG35C40Y
	500	SSG16C50	SSG16C50Y	TG16C50	SSG25C50	SSG25C50Y	TG25C50	SSG35C50	SSG35C50Y
	600	SSG16C60	SSG16C60Y	TG16C60	SSG25C60	SSG25C60Y	TG25C60	SSG35C60	SSG35C60Y
	800	SSG16C80	SSG16C80Y		SSG25C80	SSG25C80Y		SSG35C80	
	1,000	SSG16C100	SSG16C100Y		SSG25C100	SSG25C100Y		SSG35C100	
	1,200	SSG16C120	SSG16C120Y		SSG25C120	SSG25C120Y		SSG35C120	
I_{TSM} 〔A〕		140/160	140/160	140/160	220/250	220/250	220/250	350/400	300/330
I^2t 〔A^2·sec〕		106	106	106	260	260	260	660	450
di/dt 〔A/μs〕		50	50	50	50	50	50	50	50
I_{DRM} 〔mA〕		3	3	3	5	5	5	6	5
V_{TM} 〔V〕		1.7	1.7	1.5	1.6	1.6	1.4	1.6	1.4
I_{GT} 〔mA〕		50	50	50	70	70	50	70	50
V_{GT} 〔V〕		3	3	3	3	3	3	3	3
V_{GD} 〔V〕		0.2	0.2	0.2	0.2	0.2	0.2	0.2	0.2
〔dv/dt〕c 〔V/μs〕		6	6	6	20	20	6	20	5
Tj 〔℃〕		−30〜+125	−25〜+125	−25〜+125	−30〜+125	−25〜+125	−25〜+125	−30〜+125	−25〜+125
Rth 〔℃/W〕		1.2	1.8	2.0	1.0	1.4	1.6	0.8	1.4
V_{ISO} 〔V〕			2,500	2,500		2,500	2,500		2,500
Package Outline		S1, D1	Y1	T1	S2	Y2	T1	S3	Y2

SanRex TRIACS

$I_{T(RMS)}$ (A)		45amp (Tc=82°C) Harmetic Stud	50amp (Tc=85°C) Harmetic Stud	70amp (Tc=85°C) Harmetic Stud	70amp (Tc=85°C) Low Cost Harmetic Stud	100amp (Tc=83°C) Harmetic Stud	150amp (Tc=84°C) Harmetic Stud	300amp (Tc=89°C) Harmetic Stud
V_{DRM} (V)	200	SSG45C20	SSG50C20	SSG70C20	SSG70D20	SSG100C20	SSG150C20	SSG300C20
	300	SSG45C30	SSG50C30	SSG70C30	SSG70D30	SSG100C30	SSG150C30	SSG300C30
	400	SSG45C40	SSG50C40	SSG70C40	SSG70D40	SSG100C40	SSG150C40	SSG300C40
	500	SSG45C50	SSG50C50	SSG70C50	SSG70D50	SSG100C50	SSG150C50	SSG300C50
	600	SSG45C60	SSG50C60	SSG70C60	SSG70D60	SSG100C60	SSG150C60	SSG300C60
	800	SSG45C80	SSG50C80	SSG70C80		SSG100C80	SSG150C80	SSG300C80
	1,000	SSG45C100	SSG50C100	SSG70C100		SSG100C100	SSG150C100	SSG300C100
	1,200	SSG45C120	SSG50C120	SSG70C120		SSG100C120	SSG150C120	SSG300C120
I_{TSM}	(A)	500/550	720/800	900/1,000	900/1,000	1,080/1,200	1,980/2200	3,000/3,300
I^2t	(A^2·sec)	1,260	2,660	4,100	4,100	6,000	20,000	45,000
di/dt	(A/μs)	50	50	50	50	50	50	50
I_{DRM}	(mA)	6	8	10	10	10	15	25
V_{TM}	(V)	1.6	1.5	1.5	1.5	1.55	1.5	1.5
I_{GT}	(mA)	70	150	200	200	200	400	400
V_{GT}	(V)	3	3	3	3	3	3	3
V_{GD}	(V)	0.2	0.2	0.2	0.2	0.2	0.2	0.25
$(dv/dt)_c$	(V/μs)	20	20	20	20	20	50	100
Tj	(°C)	−30∼+125	−30∼+125	−30∼+125	−30∼+125	−30∼+125	−30∼+125	−30∼+125
Rth	(°C/W)	0.65	0.6	0.4	0.4	0.3	0.2	0.09
Package Outline		S3	S4	S5	S6	S5	S7	S8

$I_{T(RMS)}$ RMS On-State Current
V_{DRM} Repetitive Peak Off-State Voltage
I_{TSM} Surge On-State Current
I^2t I^2t for fusing (2∼10msec)
di/dt Critical Rate of Rse of On-State Current ($I_G = 4/3 I_{GT}$, Tj=25°C, $V_D = 1/2 V_{DRM}$ di_G/dt=1A/μs)

I_{DRM} Peak Off-State Current, max.(at V_{DRM} Single phase half wave)
V_{TM} Peak On-State Voltage, max.($I_T ≒ 1.4 I_{T(RMS)}$, Tj=25°C)
I_{GT} Gate Trigger Current, max.(Tj=25°C, I_T=1A, V_D=6V)
V_{GT} Gate Trigger Voltage, max.(Tj=25°C, I_T=1A, V_D=6V)
V_{GD} Non-Trigger Gate Voltage, min.(Tj=125°C, $V_D = 1/2 V_{DRM}$)
$(dv/dt)_c$ Critical Rate of Rise of Off-State Voltage at Commutation, min. (Tj=125°C, $V_D = 2/3 V_{DRM}$ $(di/dt)_c = 1/2 I_{T(RMS)}$ A/μs)
Rth Thermal Impedance, max.
Tj Operating Junction Temperature Range
V_{ISO} Isolation Breakdown Voltage (RMS, 1min.)

SanRex SCRs

$I_{T(AV)}$ [A]		10amp (Tc=104℃) Harmetic	16amp (Tc=88℃) Harmetic Stud	20amp (Tc=88℃) Harmetic Stud	30amp (Tc=81℃) Harmetic Stud	40amp (Tc=81℃) Harmetic Stud	70amp (Tc=83℃) Harmetic Stud	100amp (Tc=93℃) Harmetic Stud
V_{RRM} V_{DRM} (V_{RSM}) [V]	200 (240)	SC10C20	SC16C20	SC20C20	SC30C20	SC40C20	SC70C20	SC100C20
	300 (360)	SC10C30	SC16C30	SC20C30	SC30C30	SC40C30	SC70C30	SC100C30
	400 (480)	SC10C40	SC16C40	SC20C40	SC30C40	SC40C40	SC70C40	SC100C40
	500 (600)	SC10C50	SC16C50	SC20C50	SC30C50	SC40C50	SC70C50	SC100C50
	600 (720)	SC10C60	SC16C60	SC20C60	SC30C60	SC40C60	SC70C60	SC100C60
	800 (960)	SC10C80	SC16C80	SC20C80	SC30C80	SC40C80	SC70C80	SC100C80
	1,000 (1,100)	SC10C100	SC16C100	SC20C100	SC30C100	SC40C100	SC70C100	SC100C100
	1,200 (1,300)	SC10C120	SC16C120	SC20C120	SC30C120	SC40C120	SC70C120	SC100C120
$I_{T(RMS)}$	[A]	15	25	30	47	62	110	160
I_{TSM} (50/60Hz)	[A]	180/200	220/250	360/400	540/600	900/1,000	1,800/2,000	2,000/2,200
I^2t	[A^2·sec]	165	260	660	1,500	4,160	16,600	20,100
di/dt	[A/μs]	100	100	100	100	50 (V_{DRM}=200～600V)		200 (V_{DRM}=
I_{DRM}, I_{RRM}	[mA]	3	3	5	5	5	10	15
V_{TM}	[V]	1.7	1.9	1.8	1.8	1.8	1.5	1.6
I_{GT}	[mA]	40	40	50	50	70	70	100
V_{GT}	[V]	3	3	3	3	3	3	3
V_{GD}	[V]	0.2	0.2	0.25	0.25	0.25	0.25	0.25
dv/dt	[V/μs]	100 (V_{DRM}=200～600V) 200 (V_{DRM}=800～1200V)						
Tj	[℃]	−30～+125	−30～+125	−30～+125	−30～+125	−30～+125	−30～+125	−30～+125
Rth	[℃/W]	1.2	1.2	1.0	0.8	0.6	0.4	0.2
Package Outline		S1, D1	S2	S3	S3	S4	S5	S7

SanRex SCRs for welders

150amp (Tc=84℃) Harmetic Stud	300amp (Tc=85℃) Harmetic Stud
SC150C20	SC300C20
SC150C30	SC300C30
SC150C40	SC300C40
SC150C50	SC300C50
SC150C60	SC300C60
SC150C80	SC300C80
SC150C100	SC300C100
SC150C120	SC300C120
230	470
2,700/3,000	6,300/7,000
37,500	204,000
800～1,200V)	
15	25
1.6	1.45
100	100
3	3
0.25	0.25
−30～+125	−30～+125
0.17	0.09
S9	S8

$I_{T(AV)}$ [A]		60amp (Tc=115℃) Harmetic Stud	80amp (Tc=107℃) Harmetic Stud	100amp (Tc=105℃) Harmetic Stud	120amp (Tc=115℃) Harmetic Stud	250amp (Tc=97℃) Harmetic Stud
V_{RRM} V_{DRM} (V_{RSM}) [V]	200 (240)	AS60C20	AS80C20	AS100C20	AS120C20	AS250C20
	300 (360)	AS60C30	AS80C30	AS100C30	AS120C30	AS250C30
	400 (480)	AS60C40	AS80C40	AS100C40	AS120C40	AS250C40
$I_{T(RMS)}$ [A]		94	125	157	188	390
I_{TSM} (50/60Hz) [A]		1,800/2,000	2,250/2,500	2,700/3,000	3,600/4,000	5,000/5,500
I^2t [A^2·sec]		16,700	26,000	37,500	66,000	126,000
di/dt [A/μs]		50	50	50	50	50
I_{DRM}, I_{RRM} [mA]		10	10	15	15	25
V_{TM} [V]		1.47	1.34	1.30	1.22	1.40
I_{GT} [mA]		70	70	70	70	100
V_{GT} [V]		2	2	2	2	3
V_{GD} [V]		0.25	0.25	0.25	0.25	0.25
dv/dt [V/μs]		5	5	5	5	5
Tj [℃]		−30～+150	−30～+150	−30～+150	−30～+150	−30～+150
Rth [℃/W]		0.4	0.4	0.35	0.24	0.15
Package Outline		S6.1	S6.1	S11	S11	S9

- $I_{T(AV)}$ Average On-State Current
- V_{RRM} Repetitive Peak Reverse Voltage
- V_{DRM} Repetitive Peak Off-State Voltage
- V_{RSM} Non-Repetitive Peak Reverse Voltage
- $I_{T(RMS)}$ RMS On-State Current
- I_{TSM} Surge On-State Current
- I^2t I^2t for fusing (2～10msec)
- di/dt Critical Rate of Rise of On-State Current (I_G≒⅗I_{GT}, Tj=25℃, V_D=½V_{DRM} di_G/dt=1A/μs)
- I_{DRM} Repetitive Peak Off-State Current, max. (at V_{DRM}, Single phase half wave)
- I_{RRM} Repetitive Peak Reverse Current, max. (at V_{RRM}, Single phase half wave)
- V_{TM} Peak On-State Voltage, max. (I_T≒1.4$I_{T(RMS)}$, Tj=25℃)
- I_{GT} Gate Trigger Current, max. (Tj=25℃, I_T=1A, V_D=6V)
- V_{GT} Gate Trigger Voltage, max. (Tj=25℃, I_T=1A, V_D=6V)
- V_{GD} Non-Trigger Gate Voltage, min. (Tj=125℃, V_D=½V_{DRM})
- dv/dt Critical Rate of Rise of Off-State Voltage, min. (Tj=125℃, V_D=⅔V_{DRM}, Exponential wave)
- Tj Operating Junction Temperature Range
- Rth Thermal Impedunce, max.

SanRex THYRISTOR MODULES

$I_{T(AV)}$ [V]		25amp (Tc=93℃)	25amp (Tc=93℃)	40amp (Tc=83℃)	40amp (Tc=83℃)	50amp (Tc=81℃)	50amp (Tc=81℃)	70amp (Tc=81℃)	70amp (Tc=81℃)
V_{RRM} V_{DRM} (V_{RSM}) [V]	200 (240)	PK25C20	PD25C20	PK40C20	PD40C20	PK50C20	PD50C20	PK70C20	PD70C20
	400 (480)	PK25C40	PD25C40	PK40C40	PD40C40	PK50C40	PD50C40	PK70C40	PD70C40
	600 (720)	PK25C60	PD25C60	PK40C60	PD40C60	PK50C60	PD50C60	PK70C60	PD70C60
	800 (960)	PK25C80	PD25C80	PK40C80	PD40C80	PK50C80	PD50C80	PK70C80	PD70C80
$I_{T(RMS)}$	[A]	39		62		78		110	
I_{TSM} (50/60Hz)	[A]	450/500		720/800		900/1,000		1,250/1,400	
I^2t	[A^2·sec]	1,000		2,700		4,150		8,100	
di/dt	[A/μs]	100		150		150		150	
I_{DRM}, I_{RRM}	[mA]	5		8		10		12	
V_{TM}	[V]	1.55		1.50		1.45		1.40	
I_{GT}	[mA]	50		70		70		70	
V_{GT}	[V]	3		3		3		3	
V_{GD}	[V]	0.25		0.25		0.25		0.25	
dv/dt	[V/μs]	500		500		500		500	
Tj	[℃]	−30〜+125		−30〜+125		−30〜+125		−30〜+125	
Rth	[℃/W]	0.8		0.7		0.6		0.45	
V_{ISO}	[V]	2,500		2,500		2,500		2,500	
R_{ISO}	[MΩ]	1,000		1,000		1,000		1,000	
Package Outline		M1		M1		M1		M1	

$I_{T(AV)}$ Average On-State Current
V_{RRM} Repetitive Peak Reverse Voltage
V_{DRM} Repetitive Peak Off-State Voltage
V_{RSM} Non-Repetitive Peak Reverse Voltage
$I_{T(RMS)}$ RMS On-State Current
I_{TSM} Surge On-State Current
I^2t I^2t for fusing (2〜10msec)
di/dt Critical Rate of Rise of On-State Current
($I_G≒⅓I_{GT}$, Tj=25℃, $V_D=½V_{DRM}$, di_G/dt=1A/μs)
I_{DRM} Repetitive Peak Off-State Current, max.
(at V_{DRM}, Single phase half wave)
I_{RRM} Repetitive Peak Reverse Current, max.
(at V_{RRM}, Single phase half wave)

V_{TM} Peak On-State Voltage, max.($I_T≒1.4I_{T(RMS)}$, Tj=25℃)
I_{GT} Gate Trigger Current, max.(Tj=25℃, I_T=1A, V_D=6V)
V_{GT} Gate Trigger Voltage, max.(Tj=25℃, I_T=1A, V_D=6V)
V_{GD} Non-Trigger Gate Voltage, min.(Tj=125℃, $V_D=½V_{DRM}$)
dv/dt Critical Rate of Rise of Off-State Voltage, min.
(Tj=125℃, $V_D=⅔V_{DRM}$, Exponential wave)
Tj Operating Junction Temperature Range
Rth Thermal Inpedance, max.
V_{ISO} Isolation Breakdown Voltage (RMS, 1min)
R_{ISO} Isolation Resistance (D.C. 1,000V 5sec)

Fast Switching Power TRANSISTORS

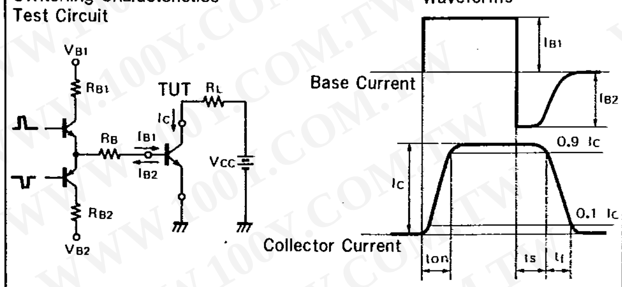
100amp (Tc=83℃)	100amp (Tc=83℃)
PK100C20	PD100C20
PK100C40	PD100C40
PK100C60	PD100C60
PK100C80	PD100C80
160	
1,800/2,000	
16,600	
200	
15	
1.40	
100	
3	
0.25	
500	
−30～+125	
0.3	
2,500	
1,000	
M1	

Ic (A)	25amp Harmetic Diamond Base			50amp Harmetic Stud		
	SQ25FE40	SQ25FE60	SQ25FE80	SQ50FE40	SQ50FE60	SQ50FE80
V_{CBO} (V)	500	700	900	500	700	900
V_{CEO} (V)	250	450	450	250	450	450
$V_{CEX(SUS)}$ (V)	400	600	800	400	600	800
$V_{CER(SUS)}$ (V)	300	500	500	300	500	500
V_{EBO} (V)	10			10		
I_C pulse (A)	50			100		
I_B (A)	10 (I_B pulse 20)			15 (I_B pulse 30)		
P_T (W)	200			350		
I_{CBO} (mA)	1.0			1.0		
I_{EBO} (mA)	1.0			1.0		
h_{FE}	8 (I_C=15A, V_{CE}=2V) 7.5 (I_C=25A, V_{CE}=5V)			9 (I_C=30A, V_{CE}=2V) 9 (I_C=50A, V_{CE}=5V)		
$V_{CE(Sat)}$ (V)	1.2			1.0		
$V_{BE(Sat)}$ (V)	1.8			1.8		
t_{on} (μs)	2.0			2.0		
t_s (μs)	3.0			3.5		
t_f (μs)	0.5			0.5		
Tj, Tstg (℃)	−30～+150			−30～+150		
Rth (℃/W)	0.63			0.36		
Package Outline	D2			S4.1		

I_C Collector Current
V_{CBO} Collector-Base Voltage
V_{CEO} Collector-Emitter Voltage
$V_{CEX(SUS)}$ Collector-Emitter Sustaining Voltage (I_C=1A, V_{EB}=8V)
$V_{CER(SUS)}$ Collector-Emitter Sustaining Voltage (I_C=1A, R_{BE}=50Ω)
V_{EBO} Emitter-Base Voltage
I_C pulse Collector Pulse Current
I_B Base Current
P_T Total Power Dissipation
I_{CBO} Collector Cutoff Current
I_{EBO} Emitter Cutoff Current
h_{FE} DC Current Gain
$V_{CE(Sat)}$ Collector-Emitter Saturation Voltage (I_C=Rating, I_B=⅕I_C)
$V_{BE(Sat)}$ Base-Emitter Saturation Voltage (I_C=Rating, I_B=⅕I_C)
t_{on} On Time
t_s Storage Time
t_f Fall Time
Tj,Tstg Operating Junction, Storage Temperature
Rth Thermal Impedance

Switching Characteristics Test Circuit

Waveforms



V_{CC}=50V
SQ25FE : I_C=20A, I_{B1}=I_{B2}=4A
SQ50FE : I_C=40A, I_{B1}=I_{B2}=8A

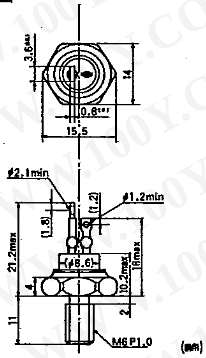
SanRex Fast Switching Thyristors

$I_{T(AV)}$ [A]		16 amp (Tc=77℃) Fast Switching SCR tq≦10μs	20 amp (Tc=75℃) Fast Switching SCR tq≦10μs	30 amp (Tc=65℃) Fast Switching SCR tq≦10μs	70 amp (Tc=74℃) Fast Switching SCR tq≦30μs	150 amp (Tc=79℃) Fast Switching SCR tq≦10μs	30 amp (Tc=85℃) High Freq Switching SCR tq≦7.5μs	20 amp (Tc=90℃) Reverse Conductive Thyristor
V_{RRM}* V_{DRM} (V_{RSM})** [V]	100 (120)	SC16C10J	SC20C10J	SC30C10J	SC70C10L	SC150C10J		
	200 (240)	SC16C20J	SC20C20J	SC30C20J	SC70C20L	SC150C20J		
	300 (360)	SC16C30J	SC20C30J	SC30C30J	SC70C30L	SC150C30J		
	400 (480)	SC16C40J	SC20C40J	SC30C40J	SC70C40L	SC150C40J	SC20C40H	SN20C40
	500 (600)	SC16C50J	SC20C50J	SC30C50J	SC70C50L	SC150C50J	SC20C50H	SN20C50
	600 (720)	SC16C60J	SC20C60J	SC30C60J	SC70C60L		SC20C60H	SN20C60
	700						SC20C70H	SN20C70
	800							SN20C80
	900							SN20C90
$I_{T(RMS)}$	[A]	25	30	47	110	230	47	30($V_{R(RMS)}$=10)
I_{TSM} (50/60Hz)	[A]	220/250	300/340	450/500	1,350/1,500	4,000/4,400	450/500	260/300
I^2t	[A²·sec]	260	480	1,040	9,370	80,600	1,040	370
di/dt	[A/μs]	50	50	50	50	200	200	28 (f≦28kHz)
I_{DRM}, I_{RRM}	[mA]	6	10	10	10	15	10	5
V_{TM}	[V]	2.5	2.5	2.5	1.8	1.8	2.5	2.2
I_{GT}	[mA]	50	70	70	70	100	150	120
V_{GT}	[V]	3	3	3	3	3	1.55	1.1
V_{GD}	[V]	0.25	0.25	0.25	0.25	0.25	0.25	0.25
tq	[μs]	10	10	10	30	10	7.5	12
dv/dt	[V/μs]	100	100	100	100	200	1,100	1,000
Tj	[℃]	−30∼+125	−30∼+125	−30∼+125	−30∼+125	−30∼+125	−30∼+125	−30∼+125
Rth	[℃/W]	1.2	1.0	0.8	0.4	0.17	0.55	0.58
Package Outline		S2	S3	S3	S5	S9	S2	S2.1

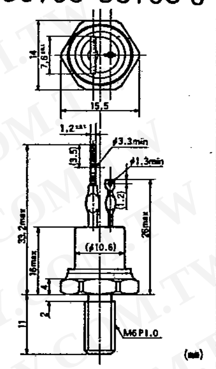
*Not Applicable for SN20C
**Not Applicable for SC20C-H or SN20C

- $I_{T(AV)}$ Average On-State Current
- V_{RRM} Repetitive Peak Reverse Voltage
- V_{DRM} Repetitive Peak Off-State Voltage
- V_{RSM} Non-Repetitive Peak Reverse Voltage
- $I_{T(RMS)}$ RMS On-State Current
- I_{TSM} Surge On-State Current
- I^2t I^2t for fusing (2∼10msec)
- di/dt Critical Rate of Rise of On-State Current (I_G≒⅘I_{GT}, Tj=25℃, V_D=½V_{DRM}, dig/dt=1A/μs)
- I_{DRM} Repetitive Peak Off-State Current, max. (at V_{DRM}, Single phase half wave)
- I_{RRM} Repetitive Peak Reverse Current, max. (at V_{RRM}, Single phase half wave)
- V_{TM} Peak On-State Voltage, max.(I_T≒1.4$I_{T(RMS)}$, Tj=25℃)
- I_{GT} Gate Trigger Current, max.(Tj=25℃, I_T=1A, V_D=6V)
- V_{GT} Gate Trigger Voltage, max.(Tj=25℃, I_T=1A, V_D=6V)
- V_{GD} Non-Trigger Gate Voltage, min.(Tj=125℃, V_D=½V_{DRM})
- tq Turn Off Time, max.(Tj=125℃, I_T=$I_{T(AV)}$ V_R=50V, V_D=½V_{DRM}, dv/dt=20V/μs)
- dv/dt Critical Rate of Rise of Off-State Voltage, min. (Tj=125℃, V_D=⅔V_{DRM}, Exponential wave)
- Tj Operating Junction Temperature Range
- Rth Thermal Impedunce, max.

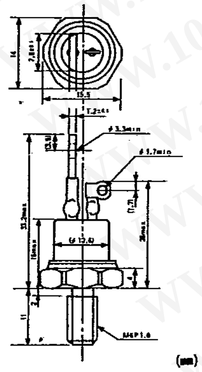
S1 SSG16C SC10C



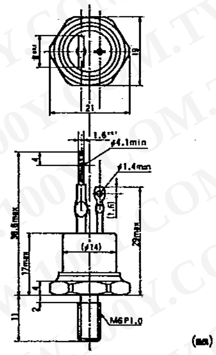
S2 SSG25C·SC20C-H SC16C·SC16C-J



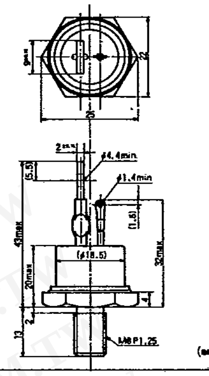
S2.1 SN20C



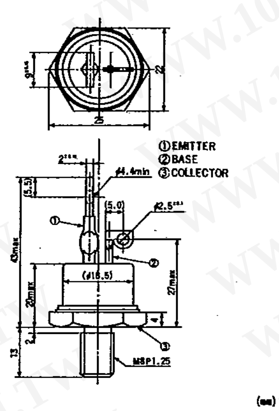
S3 SSG35C SSG45C SC20C SC30C SC20C-J SC30C-J



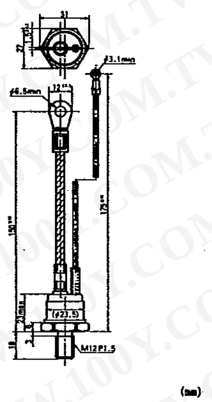
S4 SSG50C SC40C



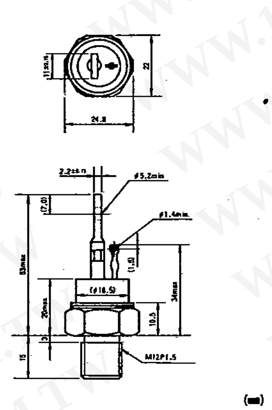
S4.1 SQ50FE



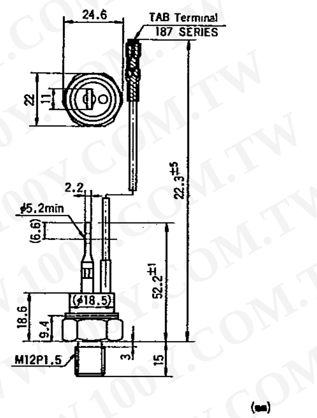
S5 SSG70C SSG100C SC70C SC70C-L



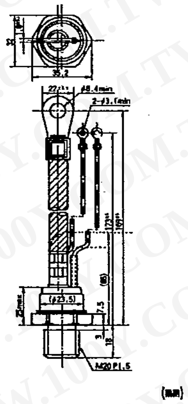
S6 SSG70D



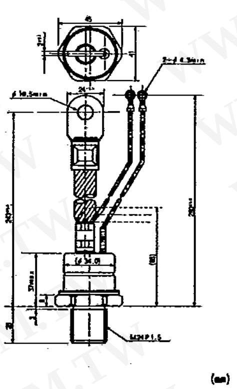
S6.1 AS60C AS80C



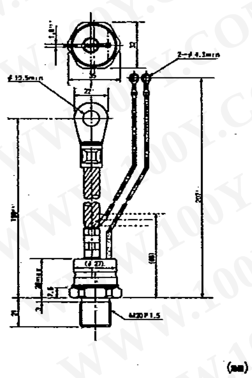
S7 SSG150C SC100C



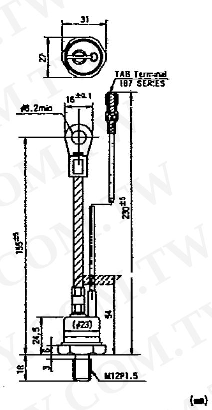
S8 SSG300C SC300C



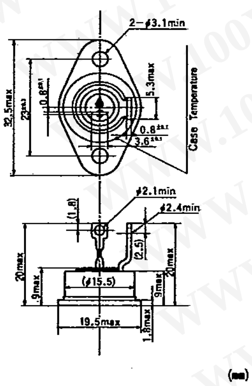
S9 SC150C SC150-J AS250C



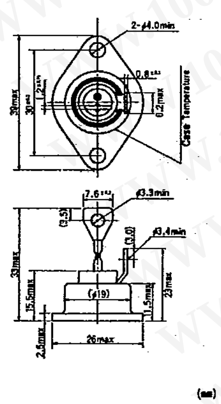
S11 AS100C AS120C



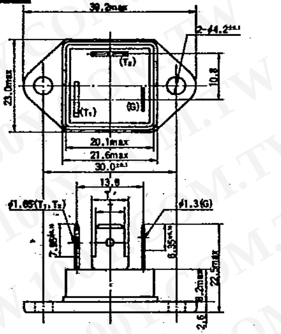
Y1 SSG16C-Y



Y2 SSG25C-Y SSG35C-Y

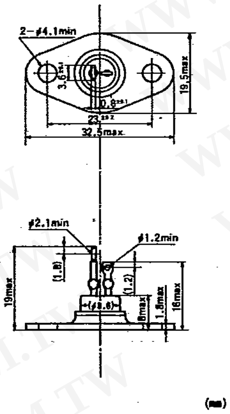


T1 TG16C·TG25C

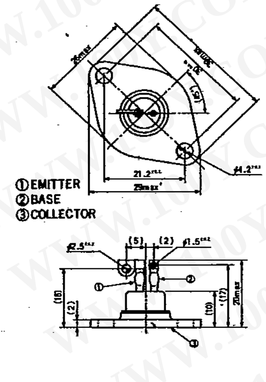


T₁ : TAB250(T=6.35,T'=8.25, t=0.8)
T₂ : TAB250(T=6.35,T'=8.25, t=0.8)
G : TAB187(T=4.75,T'=5.7, t=0.5) (mm)

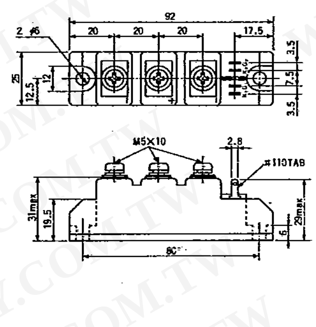
D1 SSG16C-D SC10C-D



D2 SQ25FE



M1 PKseries



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